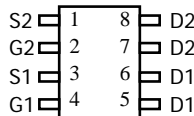


## General Description

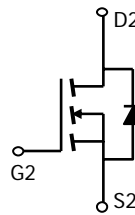
The AO4603 uses advanced trench technology MOSFETs to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications. *Standard product AO4603 is Pb-free (meets ROHS & Sony 259 specifications). AO4603L is a Green Product ordering option. AO4603 and AO4603L are electrically identical.*

## Features

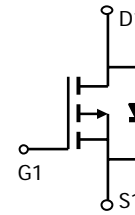
n-channel	p-channel
$V_{DS} (V) = 30V$	-30V
$I_D = 4.7A (V_{GS}=10V)$	-5.8A ( $V_{GS} = -10V$ )
$R_{DS(ON)}$	$R_{DS(ON)}$
< 55m $\Omega$ ( $V_{GS}=10V$ )	< 35m $\Omega$ ( $V_{GS} = -10V$ )
< 70m $\Omega$ ( $V_{GS}=4.5V$ )	< 58m $\Omega$ ( $V_{GS} = -4.5V$ )
< 110m $\Omega$ ( $V_{GS} = 2.5V$ )	



SOIC-8



n-channel



p-channel

### Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	$V_{DS}$	30	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$I_D$	$T_A=25^\circ C$	4.7	-5.8
		$T_A=70^\circ C$	4	-4.9
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	30	-40	A
Power Dissipation	$P_D$	$T_A=25^\circ C$	2	2
		$T_A=70^\circ C$	1.44	1.44
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ C$

### Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	n-ch	52	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		n-ch	78	110	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	n-ch	48	50	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	p-ch	50	62.5	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>		p-ch	73	110	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	p-ch	31	35	$^\circ C/W$

n-channel MOSFET Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.6	1	1.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	10			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=4\text{A}$ $T_J=125^\circ\text{C}$		45	55	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=3\text{A}$		55	70	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_D=2\text{A}$		83	110	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=4\text{A}$		8		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.8	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{ISS}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=15\text{V}$ , $f=1\text{MHz}$		390		pF
$C_{OSS}$	Output Capacitance			54.5		pF
$C_{RSS}$	Reverse Transfer Capacitance			41		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		3		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}$ , $V_{DS}=15\text{V}$ , $I_D=4\text{A}$		0.6		nC
$Q_{gs}$	Gate Source Charge			1.38		nC
$Q_{gd}$	Gate Drain Charge			4.34		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $R_L=3.75\Omega$ , $R_{GEN}=6\Omega$		3.3		ns
$t_r$	Turn-On Rise Time			1		ns
$t_{D(off)}$	Turn-Off DelayTime			21.7		ns
$t_f$	Turn-Off Fall Time			2.1		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=4\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		12		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=4\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		6.3		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

Rev3: August 2005

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS N-Channel

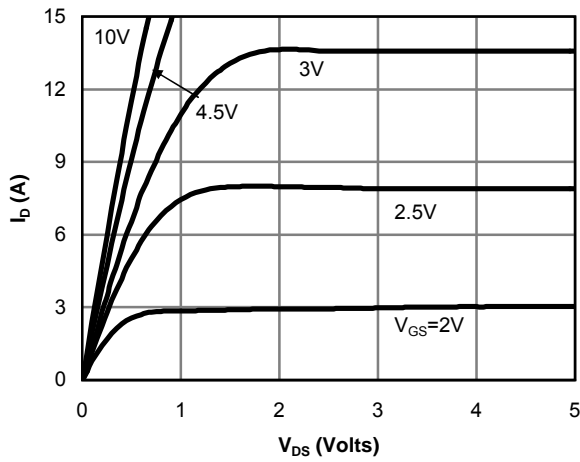


Fig 1: On-Region Characteristics

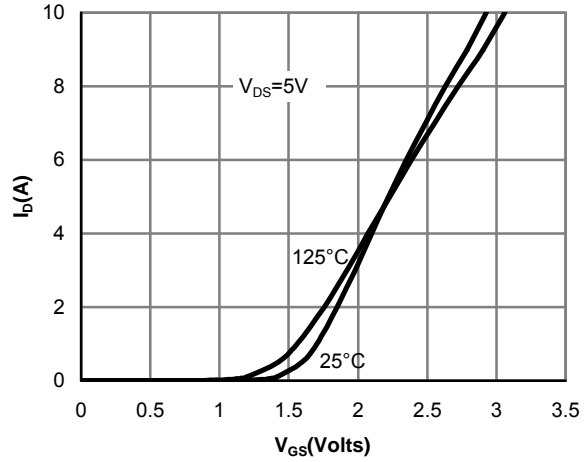


Figure 2: Transfer Characteristics

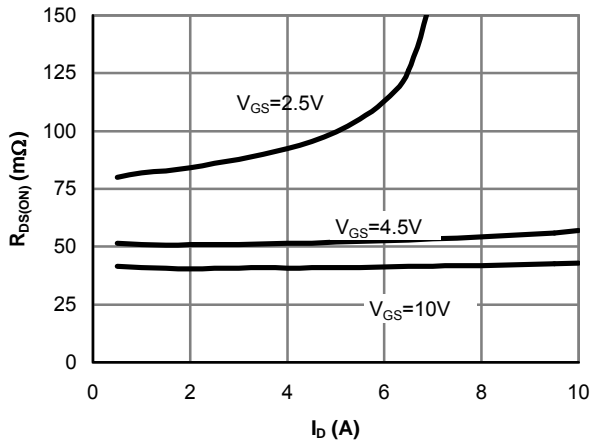


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

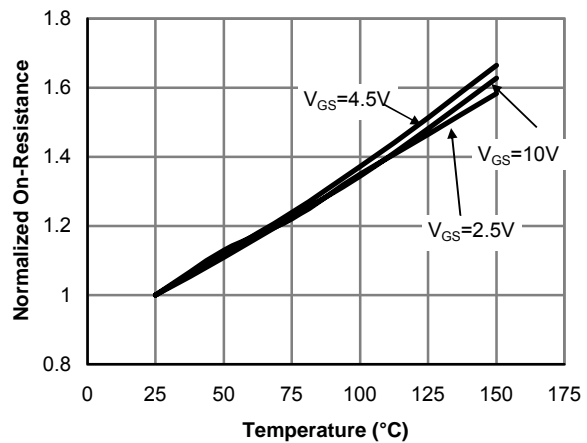


Figure 4: On-Resistance vs. Junction Temperature

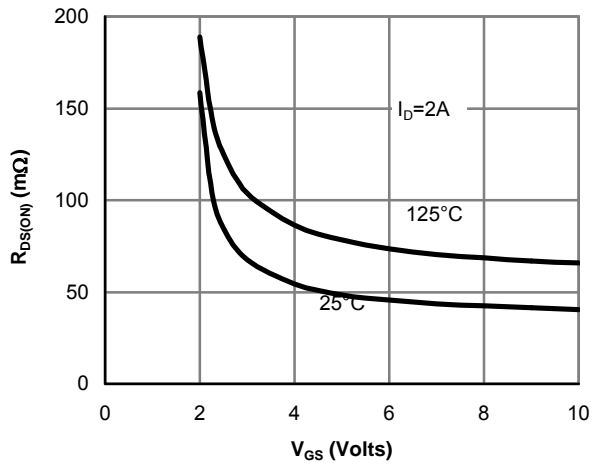


Figure 5: On-Resistance vs. Gate-Source Voltage

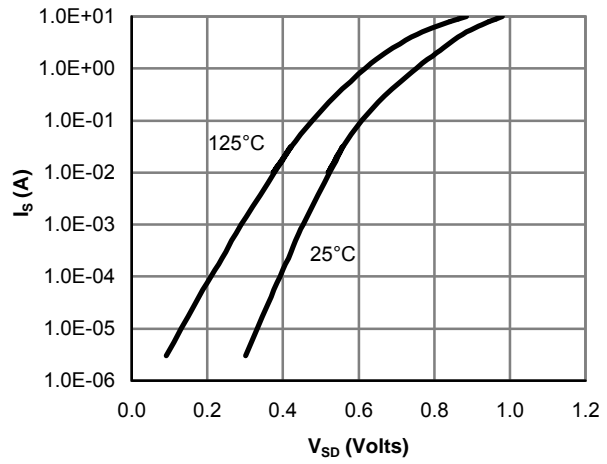


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS N-Channel

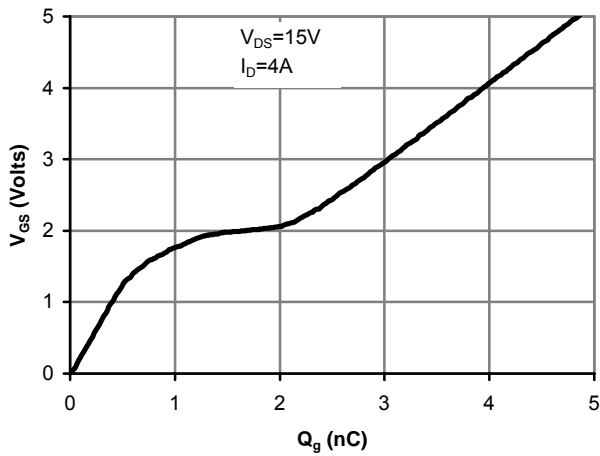


Figure 7: Gate-Charge Characteristics

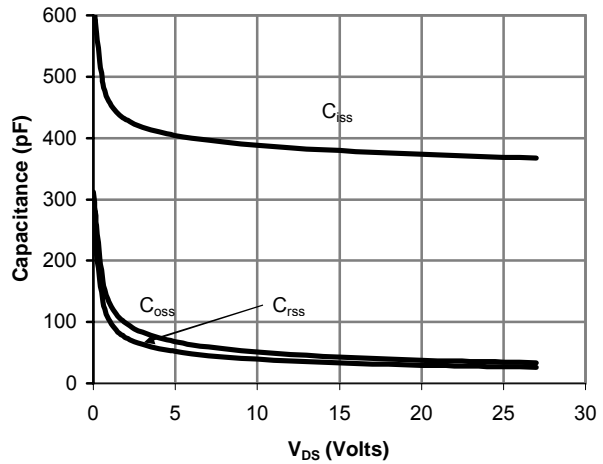


Figure 8: Capacitance Characteristics

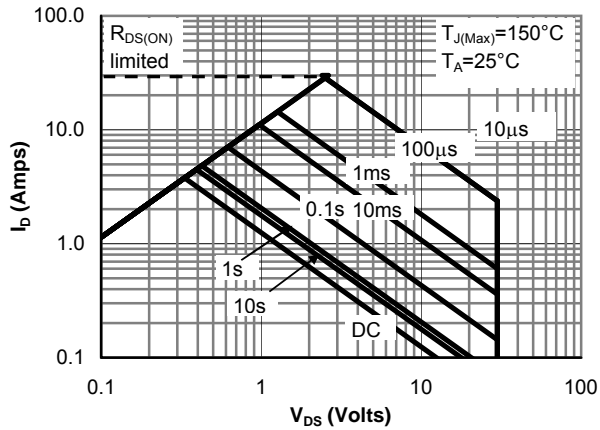


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

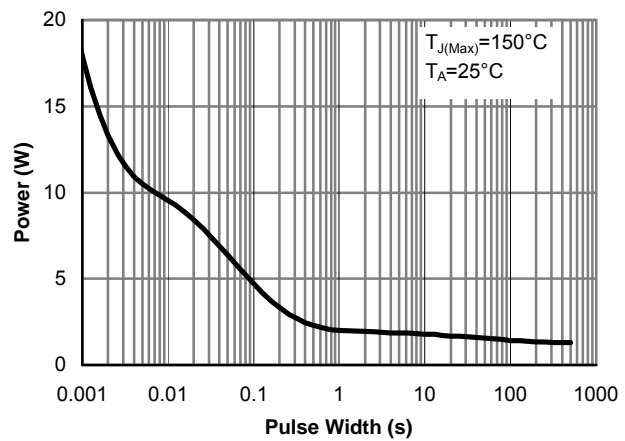


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

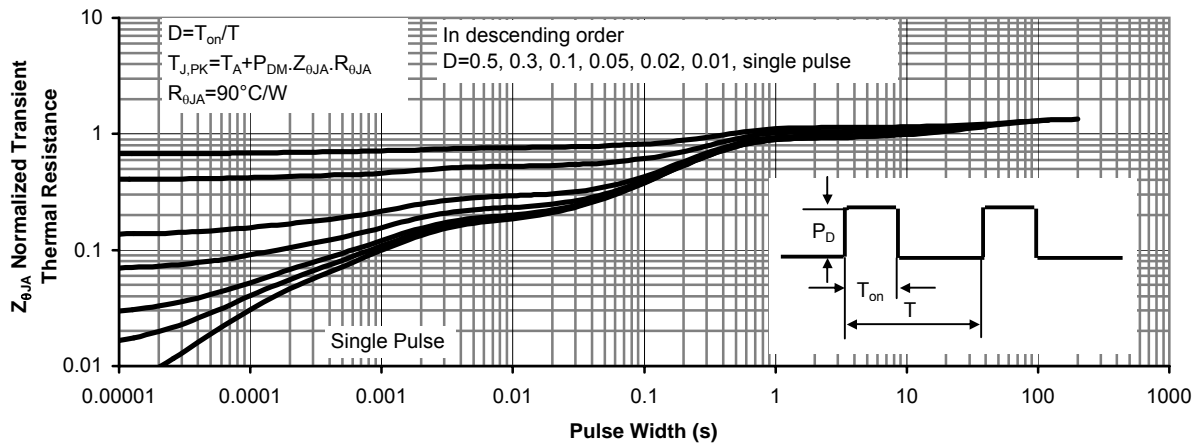


Figure 11: Normalized Maximum Transient Thermal Impedance

p-channel MOSFET Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.2	-1.8	-2.2	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}, V_{DS}=-5\text{V}$	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}, I_D=-5\text{A}$ $T_J=125^\circ\text{C}$		29 40	38	m $\Omega$
		$V_{GS}=-4.5\text{V}, I_D=-5\text{A}$		39	63	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=-5\text{V}, I_D=-10\text{A}$				S
$V_{SD}$	Diode Forward Voltage	$I_S=-1\text{A}, V_{GS}=0\text{V}$		-0.75	-1	V
$I_S$	Maximum Body-Diode Continuous Current				-4.2	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		920		pF
$C_{oss}$	Output Capacitance			190		pF
$C_{rss}$	Reverse Transfer Capacitance			122		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		3.6		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, I_D=-7.5\text{A}$		2.4		nC
$Q_{gs}$	Gate Source Charge			4.5		nC
$Q_{gd}$	Gate Drain Charge			9.3		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, R_L=2\Omega,$ $R_{GEN}=3\Omega$		7.6		ns
$t_r$	Turn-On Rise Time			5.2		ns
$t_{D(off)}$	Turn-Off Delay Time			21.6		ns
$t_f$	Turn-Off Fall Time			8		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=-7.5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		20		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=-7.5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		8.8		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any a given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS P-Channel

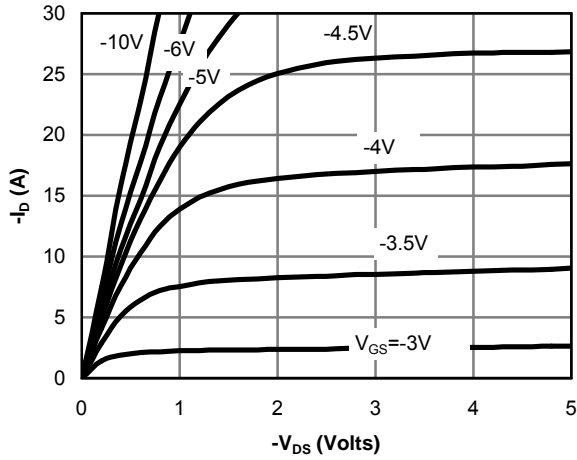


Fig 1: On-Region Characteristics

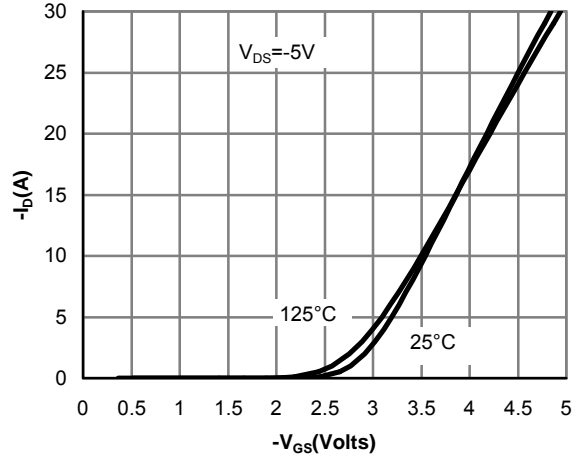


Figure 2: Transfer Characteristics

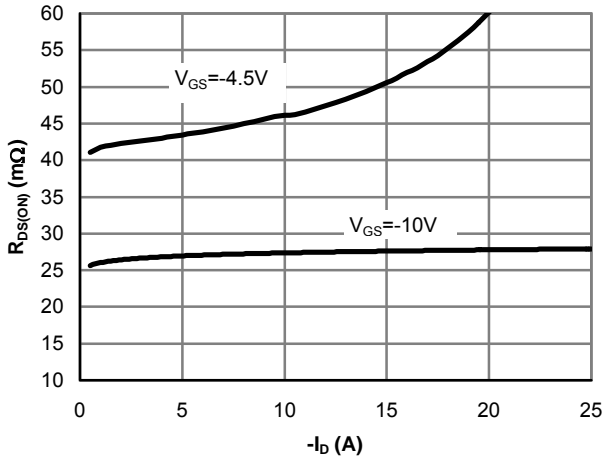


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

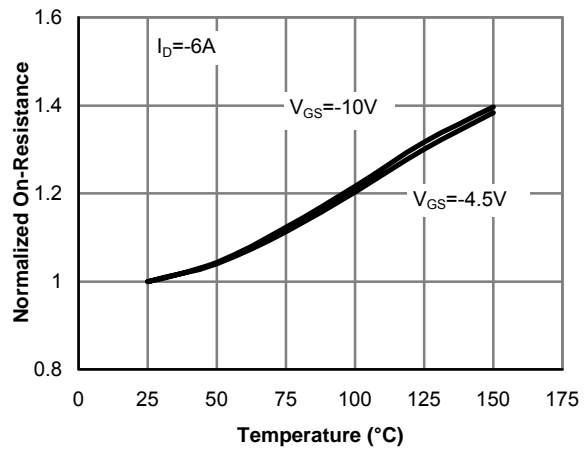


Figure 4: On-Resistance vs. Junction Temperature

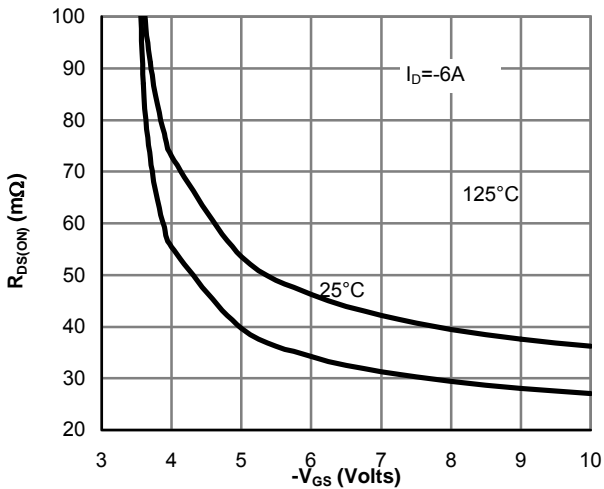


Figure 5: On-Resistance vs. Gate-Source Voltage

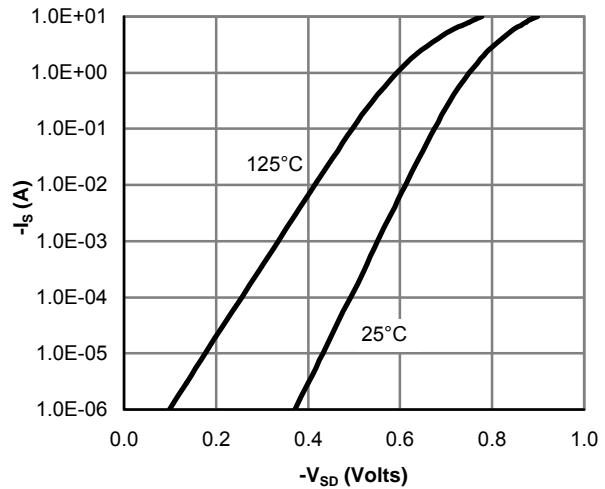


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS P-Channel

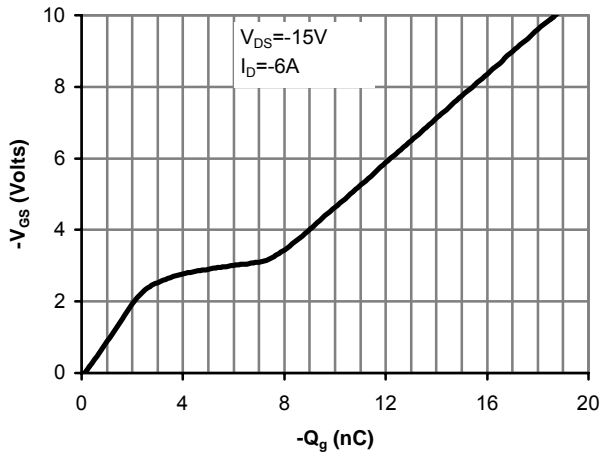


Figure 7: Gate-Charge Characteristics

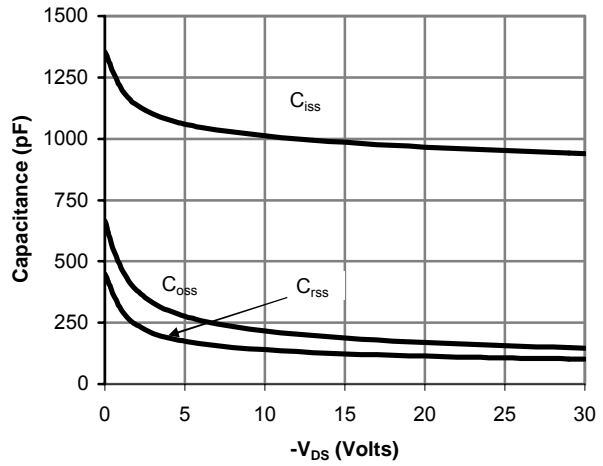


Figure 8: Capacitance Characteristics

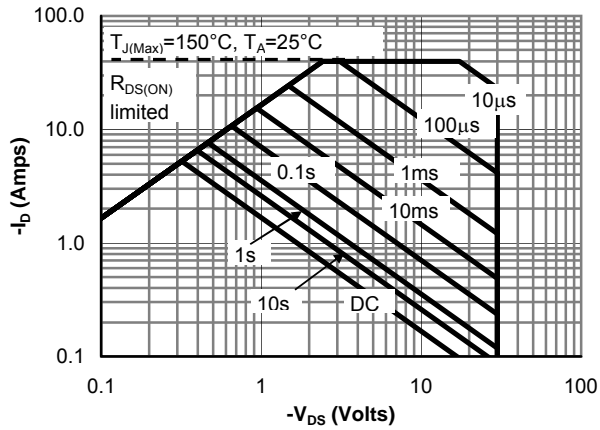


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

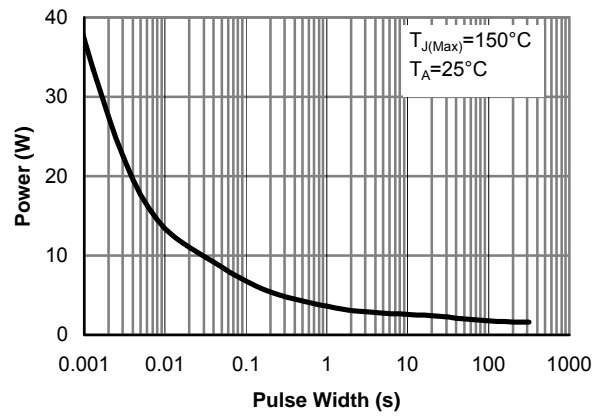


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

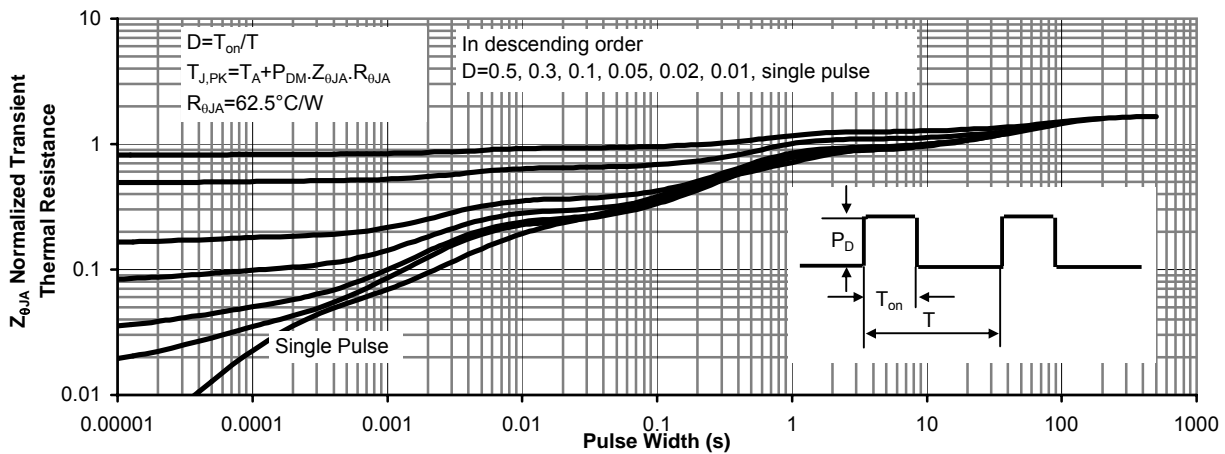


Figure 11: Normalized Maximum Transient Thermal Impedance